

2MBI150U4H-120

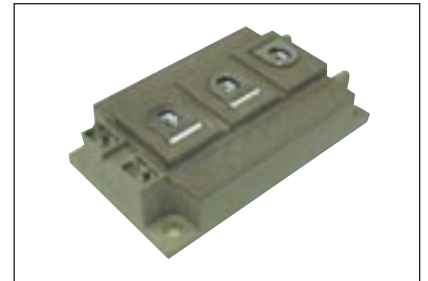
IGBT MODULE (U series) 1200V / 150A / 2 in one package

■ Features

- High speed switching
- Voltage drive
- Low Inductance module structure

■ Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply
- Industrial machines, such as Welding machines



■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items	Symbols	Conditions	Maximum ratings	Units		
Collector-Emitter voltage	V _{CEs}		1200	V		
Gate-Emitter voltage	V _{GES}		±20	V		
Collector current	I _c	Continuous	T _c =25°C	200	A	
			T _c =80°C	150		
	I _c pulse	1ms	T _c =25°C	400		
			T _c =80°C	300		
	-I _c			150		
-I _c pulse	1ms		300			
Collector power dissipation	P _c	1 device	780	W		
Junction temperature	T _j		+150	°C		
Storage temperature	T _{stg}		-40 to +125	°C		
Isolation voltage	Between terminal and copper base (*1)		V _{iso}	AC : 1min.	2500	VAC
Screw torque	Mounting (*2)		3.5	N·m		
	Terminals (*2)		4.5			

Note *1: All terminals should be connected together when isolation test will be done.

Note *2: Recommendable value : Mounting : 2.5-3.5 N·m (M5 or M6), Terminals : 3.5-4.5 N·m (M6)

● Electrical characteristics (at Tj= 25°C unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units	
			min.	typ.	max.		
Zero gate voltage collector current	I _{CEs}	V _{GE} = 0V, V _{CE} = 1200V	-	-	2.0	mA	
Gate-Emitter leakage current	I _{GES}	V _{CE} = 0V, V _{GE} = ±20V	-	-	400	nA	
Gate-Emitter threshold voltage	V _{GE(th)}	V _{CE} = 20V, I _c = 150mA	4.5	6.5	8.5	V	
Collector-Emitter saturation voltage	V _{CE(sat)} (terminal)	V _{GE} = 15V I _c = 150A	T _j =25°C	-	2.00	2.15	V
			T _j =125°C	-	2.20	-	
	V _{CE(sat)} (chip)		T _j =25°C	-	1.90	2.05	
			T _j =125°C	-	2.10	-	
Input capacitance	C _{ies}	V _{GE} = 0V, V _{CE} = 10V, f = 1MHz	-	17	-	nF	
Turn-on time	t _{on}	V _{CC} = 600V I _c = 150A V _{GE} = ±15V R _G = 4.7Ω	-	0.32	1.20	μs	
	t _r		-	0.10	0.60		
Turn-off time	t _{r(i)}		-	0.03	-		
	t _{off}		-	0.41	1.00		
Forward on voltage	V _F (terminal)	V _{GE} = 0V I _F = 150A	T _j =25°C	-	1.75	1.90	V
			T _j =125°C	-	1.85	-	
	V _F (chip)		T _j =25°C	-	1.65	1.80	
			T _j =125°C	-	1.75	-	
Reverse recovery time	t _{rr}	I _F = 150A	-	-	0.35	μs	
Lead resistance, terminal-chip (*3)	R lead		-	0.53	-	mΩ	

Note *3: Biggest internal terminal resistance among arm.

● Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance (1device)	R _{th(j-c)}	IGBT	-	-	0.16	°C/W
		FWD	-	-	0.24	
Contact thermal resistance (1device)	R _{th(c-f)}	with Thermal Compound (*4)	-	0.025	-	

Note *4: This is the value which is defined mounting on the additional cooling fin with thermal compound.